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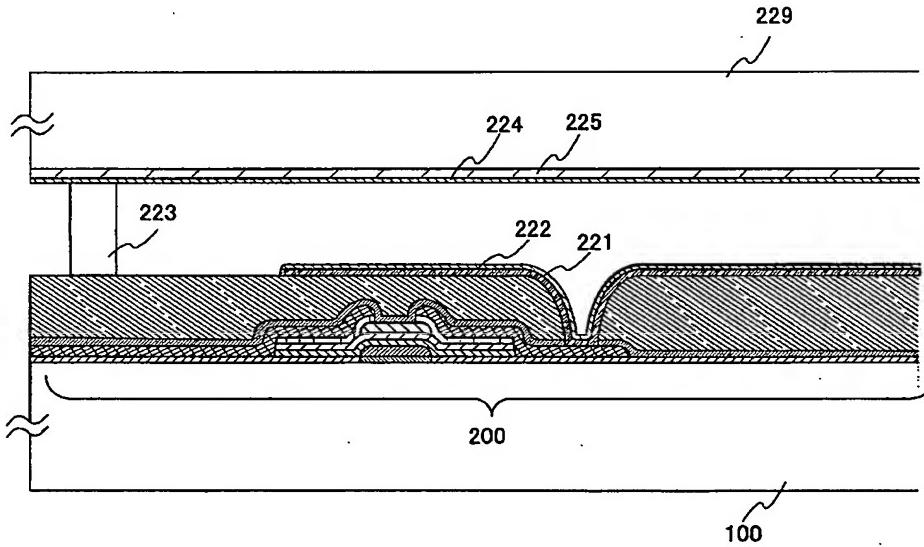
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(54) Title: DISPLAY DEVICE AND METHOD FOR MANUFACTURING THE SAME



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(57) Abstract: According to one aspect of the present invention, at least one or more of patterns required for manufacturing a display device, such as a conductive layer which forms a wiring or an electrode and a mask, is formed by a droplet discharging method. At that time, a portion of the gate insulating film where is not located under the semiconductor layer is removed by during manufacturing steps of the present invention.



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